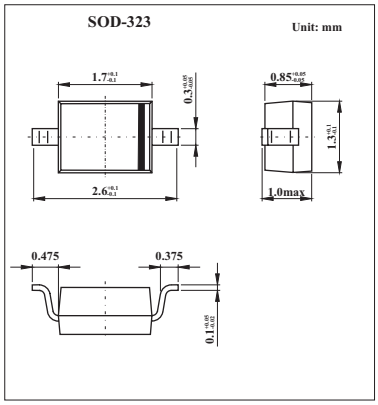
SCHOTTKY DIODE

SD106WS



Features

- Low turn-on voltage
- Fast switching
- Microminiature plastic package
- There devices are protected by a PN junction guard ring against excessive voltage, such as electrostatic discharge.
- Ideal for protection of MOS devices, steering, blasing,and couplong diodes for fast switching and low logic level applocations.

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Continuous Reverse Voltage	V_R	30	Volts
Forward Current	I_F	200	mA
Forward Surge Current, tp = 10 ms	I_{FSM}	1.0	A
Power Dissipation Tc = 25 ℃	P_{tot}	250(Note 1)	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	500	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature Range	T_S	-65 to +150	℃

Note:

1. Valid provided that electrodes are kept at ambient temperature

Electrical Characteristics Ta = 25℃

Characteristic		Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage	at I_R = 100 μA	BV_R	30			Volts
Leakage Current	at V_R = 30 V	I_R			5.0	μA
Forward Voltage	at I_F = 2.1 mA	V_F		260		mV
	at I_F = 15 mA			320		
	at I_F = 100 mA			420		
	at I_F = 200 mA			490	550	
Junction Capacitance at V_R = 10 V, f = 1.0 MHz		C_{tot}			15	pF

Marking

Marking	S2